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Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	C28x
Core Size	32-Bit Single-Core
Speed	60MHz
Connectivity	CANbus, I²C, LINbus, SCI, SPI, UART/USART
Peripherals	Brown-out Detect/Reset, POR, PWM, WDT
Number of I/O	45
Program Memory Size	128KB (64K x 16)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	10K x 16
Voltage - Supply (Vcc/Vdd)	1.71V ~ 1.995V
Data Converters	A/D 16x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 125°C (TA)
Mounting Type	Surface Mount
Package / Case	80-LQFP
Supplier Device Package	80-LQFP (12x12)
Purchase URL	https://www.e-xfl.com/product-detail/texas-instruments/tms320f28035pnqr

About this Document

This Data Sheet is addressed to embedded hardware and software developers. It provides the reader with detailed descriptions about the ordering designations, available features, electrical and physical characteristics of the XMC1200 series devices.

The document describes the characteristics of a superset of the XMC1200 series devices. For simplicity, the various device types are referred to by the collective term XMC1200 throughout this document.

XMC™1000 Family User Documentation

The set of user documentation includes:

- **Reference Manual**
  – decribes the functionality of the superset of devices.
- **Data Sheets**
  – list the complete ordering designations, available features and electrical characteristics of derivative devices.
- **Errata Sheets**
  – list deviations from the specifications given in the related Reference Manual or Data Sheets. Errata Sheets are provided for the superset of devices.

Attention: Please consult all parts of the documentation set to attain consolidated knowledge about your device.

Application related guidance is provided by **Users Guides** and **Application Notes**.

Please refer to **http://www.infineon.com/xmc1000** to get access to the latest versions of those documents.

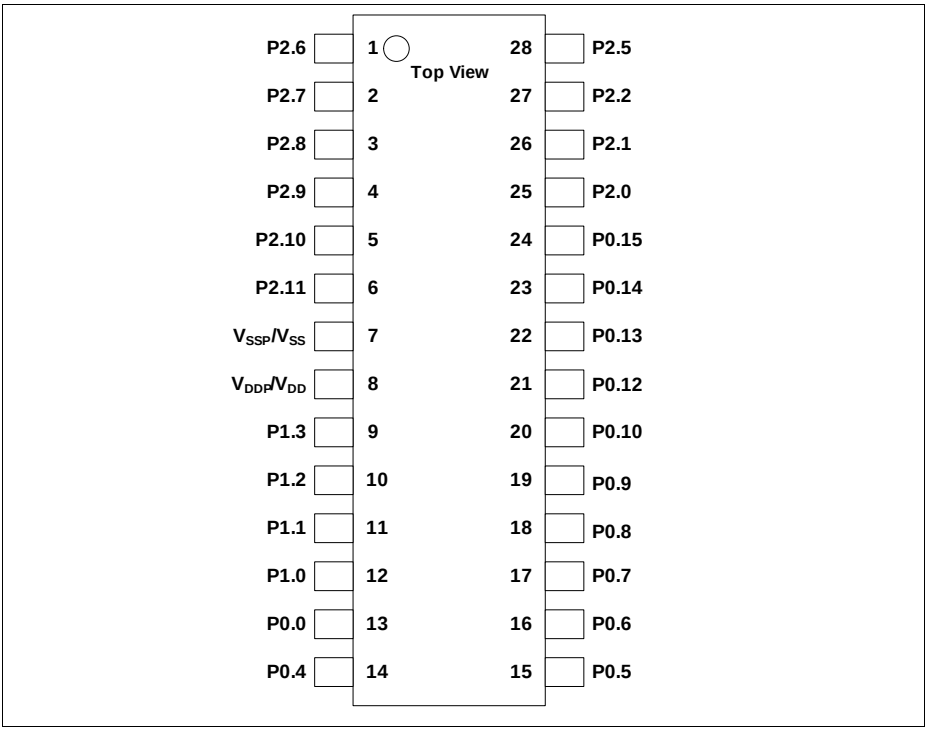

Figure 5 XMC1200 PG-TSSOP-28 Pin Configuration (top view)

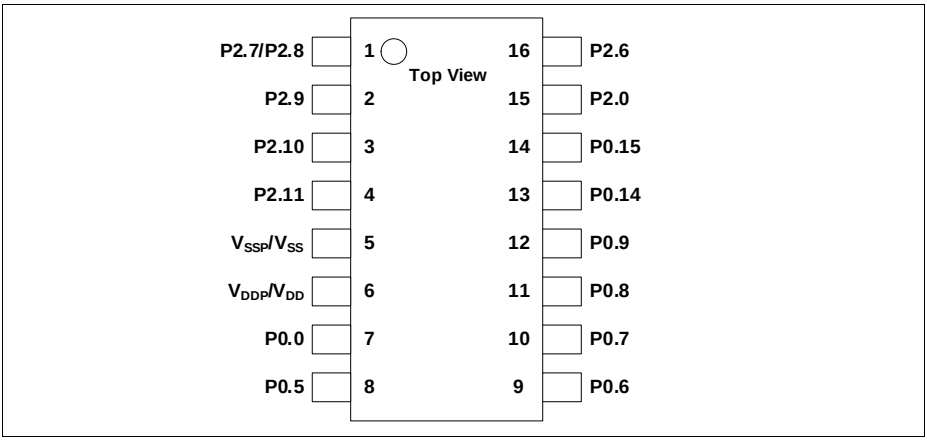

Figure 6 XMC1200 PG-TSSOP-16 Pin Configuration (top view)

Table 6 Package Pin Mapping (cont'd)

Function	VQFN 40	TSSOP 38	TSSOP 28	VQFN 24	TSSOP 16	Pad Type	Notes
P0.7	30	24	17	18	10	STD_INOUT	
P0.8	33	27	18	19	11	STD_INOUT	
P0.9	34	28	19	20	12	STD_INOUT	
P0.10	35	29	20	-	-	STD_INOUT	
P0.11	36	30	-	-	-	STD_INOUT	
P0.12	37	31	21	21	-	STD_INOUT	
P0.13	38	32	22	22	-	STD_INOUT	
P0.14	39	33	23	23	13	STD_INOUT	
P0.15	40	34	24	24	14	STD_INOUT	
P1.0	22	16	12	14	-	High Current	
P1.1	21	15	11	13	-	High Current	
P1.2	20	14	10	12	-	High Current	
P1.3	19	13	9	11	-	High Current	
P1.4	18	12	-	-	-	High Current	
P1.5	17	11	-	-	-	High Current	
P1.6	16	-	-	-	-	STD_INOUT	
P2.0	1	35	25	1	15	STD_INOUT/AN	

Table 6 Package Pin Mapping (cont'd)

Function	VQFN 40	TSSOP 38	TSSOP 28	VQFN 24	TSSOP 16	Pad Type	Notes
P2.1	2	36	26	2	-	STD_INOUT/AN	
P2.2	3	37	27	3	-	STD_IN/AN	
P2.3	4	38	-	-	-	STD_IN/AN	
P2.4	5	1	-	-	-	STD_IN/AN	
P2.5	6	2	28	-	-	STD_IN/AN	
P2.6	7	3	1	4	16	STD_IN/AN	
P2.7	8	4	2	5	1	STD_IN/AN	
P2.8	9	5	3	5	1	STD_IN/AN	
P2.9	10	6	4	6	2	STD_IN/AN	
P2.10	11	7	5	7	3	STD_INOUT/AN	
P2.11	12	8	6	8	4	STD_INOUT/AN	
VSS	13	9	7	9	5	Power	Supply GND, ADC reference GND
VDD	14	10	8	10	6	Power	Supply VDD, ADC reference voltage/ ORC reference voltage
VDDP	15	10	8	10	6	Power	When VDD is supplied, VDDP has to be supplied with the same voltage.

2.2.3 Hardware Controlled I/O Function Description

The following general building block is used to describe the hardware I/O and pull control functions of each PORT pin:

Table 8 Hardware Controlled I/O Function Description

Function	Outputs	Inputs	Pull Control	
	HWO0	**HWI0**	**HW0_PD**	**HW0_PU**
P0.0	MODB.OUT	MODB.INA		
Pn.y			$\overline{\text{MODC.OUT}}$	MODC.OUT

By Pn_HWSEL, it is possible to select between different hardware “masters” (HWO0/HWI0, HWO1/HWI1). The selected peripheral can take control of the pin(s). Hardware control overrules settings in the respective port pin registers. Additional hardware signals HW0_PD/HW1_PD and HW0_PU/HW1_PU controlled by the peripherals can be used to control the pull devices of the pin.

Please refer to the **Hardware Controlled I/O Functions** table for the complete hardware I/O and pull control function mapping.

Table 13 PN-Junction Characterisitics for positive Overload

Pad Type	I_{OV} = 5 mA, T_J = -40 °C	I_{OV} = 5 mA, T_J = 115 °C
Standard, High-current, AN/DIG_IN	$V_{IN} = V_{DDP} + 0.5$ V	$V_{IN} = V_{DDP} + 0.5$ V

Table 14 PN-Junction Characterisitics for negative Overload

Pad Type	I_{OV} = 5 mA, T_J = -40 °C	I_{OV} = 5 mA, T_J = 115 °C
Standard, High-current, AN/DIG_IN	$V_{IN} = V_{SS} - 0.5$ V	$V_{IN} = V_{SS} - 0.5$ V

Table 16 Input/Output Characteristics (Operating Conditions apply) (cont'd)

Parameter	Symbol		Limit Values		Unit	Test Conditions
			Min.	Max.		
Input low voltage on port pins (Large Hysteresis)	V_{ILPL}	SR	–	0.08 × V_{DDP}	V	CMOS Mode (5 V, 3.3 V & 2.2 V)[10]
Input high voltage on port pins (Large Hysteresis)	V_{IHPL}	SR	0.85 × V_{DDP}	–	V	CMOS Mode (5 V, 3.3 V & 2.2 V)[10]
Rise time on High Current Pad[1]	t_{HCPR}	CC	–	9	ns	50 pF @ 5 V[2]
			–	12	ns	50 pF @ 3.3 V[3]
			–	25	ns	50 pF @ 1.8 V[4]
Fall time on High Current Pad[1]	t_{HCPF}	CC	–	9	ns	50 pF @ 5 V[2]
			–	12	ns	50 pF @ 3.3 V[3]
			–	25	ns	50 pF @ 1.8 V[4]
Rise time on Standard Pad[1]	t_R	CC	–	12	ns	50 pF @ 5 V[5]
			–	15	ns	50 pF @ 3.3 V[6]
			–	31	ns	50 pF @ 1.8 V[7]
Fall time on Standard Pad[1]	t_F	CC	–	12	ns	50 pF @ 5 V[5]
			–	15	ns	50 pF @ 3.3 V[6]
			–	31	ns	50 pF @ 1.8 V[7]
Input Hysteresis[8]	HYS	CC	0.08 × V_{DDP}	–	V	CMOS Mode (5 V), Standard Hysteresis
			0.03 × V_{DDP}	–	V	CMOS Mode (3.3 V), Standard Hysteresis
			0.02 × V_{DDP}	–	V	CMOS Mode (2.2 V), Standard Hysteresis
			0.5 × V_{DDP}	0.75 × V_{DDP}	V	CMOS Mode(5 V), Large Hysteresis
			0.4 × V_{DDP}	0.75 × V_{DDP}	V	CMOS Mode(3.3 V), Large Hysteresis
			0.2 × V_{DDP}	0.65 × V_{DDP}	V	CMOS Mode(2.2 V), Large Hysteresis

3.2.2 Analog to Digital Converters (ADC)

Table 17 shows the Analog to Digital Converter (ADC) characteristics.

Note: These parameters are not subject to production test, but verified by design and/or characterization.

Table 17 ADC Characteristics (Operating Conditions apply)[1)]

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Supply voltage range (internal reference)	V_{DD_int} SR	2.0	–	3.0	V	SHSCFG.AREF = 11_B CALCTR.CALGNSTC = $0C_H$
		3.0	–	5.5	V	SHSCFG.AREF = 10_B
Supply voltage range (external reference)	V_{DD_ext} SR	3.0	–	5.5	V	SHSCFG.AREF = 00_B
Analog input voltage range	V_{AIN} SR	V_{SSP} - 0.05	–	V_{DDP} + 0.05	V	
Auxiliary analog reference ground	V_{REFGND} SR	V_{SSP} - 0.05	–	1.0	V	G0CH0
		V_{SSP} - 0.05	–	0.2	V	G1CH0
Internal reference voltage (full scale value)	V_{REFINT} CC	5			V	
Switched capacitance of an analog input	C_{AINS} CC	–	1.2	2	pF	GNCTRxz.GAINy = 00_B (unity gain)
		–	1.2	2	pF	GNCTRxz.GAINy = 01_B (gain g1)
		–	4.5	6	pF	GNCTRxz.GAINy = 10_B (gain g2)
		–	4.5	6	pF	GNCTRxz.GAINy = 11_B (gain g3)
Total capacitance of an analog input	C_{AINT} CC	–	–	10	pF	
Total capacitance of the reference input	C_{AREFT} CC	–	–	10	pF	

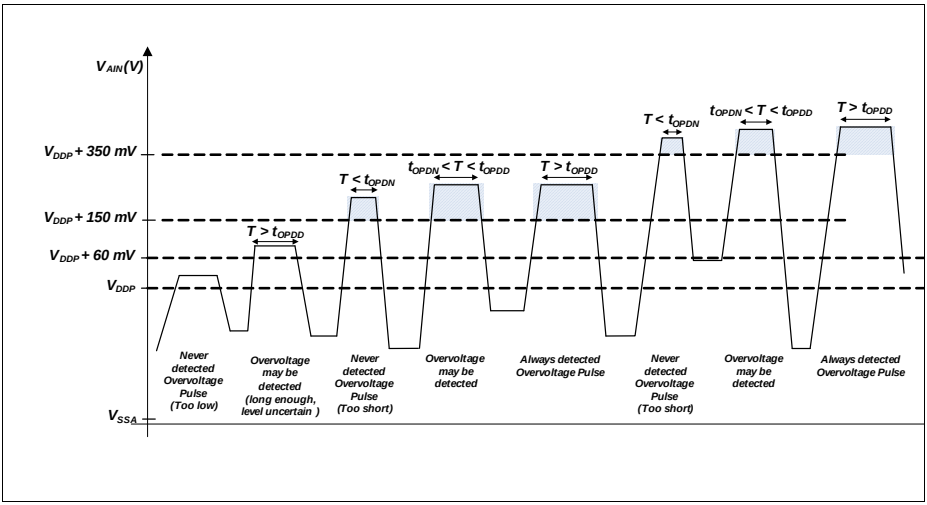

Figure 13 ORC Detection Ranges

3.2.7 Flash Memory Parameters

Note: These parameters are not subject to production test, but verified by design and/or characterization.

Table 23 Flash Memory Parameters

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Erase Time per page / sector	t_{ERASE} CC	6.8	7.1	7.6	ms	
Program time per block	t_{PSER} CC	102	152	204	µs	
Wake-Up time	t_{WU} CC	–	32.2	–	µs	
Read time per word	t_a CC	–	50	–	ns	
Data Retention Time	t_{RET} CC	10	–	–	years	Max. 100 erase / program cycles
Flash Wait States [1]	$N_{WSFLASH}$ CC	0	0	0		f_{MCLK} = 8 MHz
		0	1	1		f_{MCLK} = 16 MHz
		1	1.3	2		f_{MCLK} = 32 MHz
Fixed Flash Wait States configured in bit NVM_NVMCONF.WS	$N_{FWSFLASH}$ SR	0	0	1		NVM_CONFIG1. FIXWS = 1_B, $f_{MCLK} \leq$ 16 MHz
		1	1	1		NVM_CONFIG1. FIXWS = 1_B, 16 MHz < $f_{MCLK} \leq$ 32 MHz
Erase Cycles	N_{ECYC} CC	–	–	$5*10^4$	cycles	Sum of page and sector erase cycles
Total Erase Cycles	N_{TECYC} CC	–	–	$2*10^6$	cycles	

1) Flash wait states are automatically inserted by the Flash module during memory read when needed. Typical values are calculated from the execution of the Dhrystone benchmark program.

3.3 AC Parameters

3.3.1 Testing Waveforms

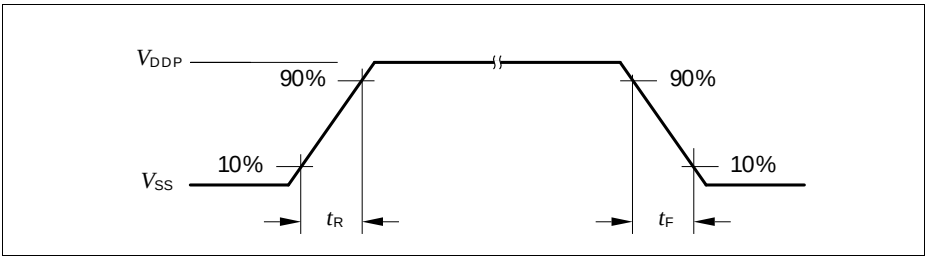

Figure 16 Rise/Fall Time Parameters

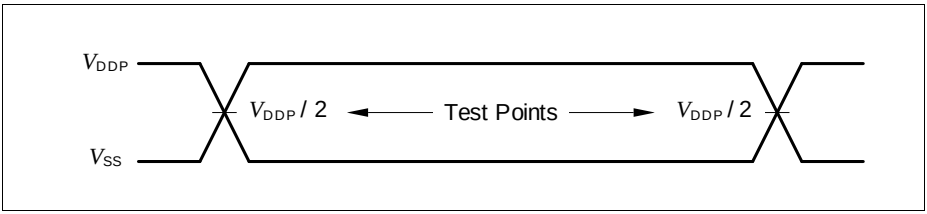

Figure 17 Testing Waveform, Output Delay

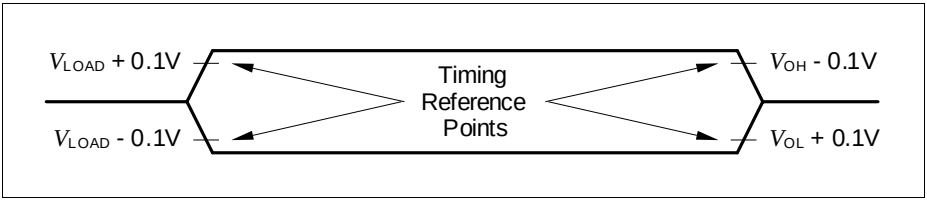

Figure 18 Testing Waveform, Output High Impedance

Table 24 Power-Up and Supply Monitoring Parameters (Operating Conditions apply)[1)] (cont'd)

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
V_{DDP} brownout reset voltage	V_{DDPBO} CC	1.55	1.62	1.75	V	calibrated, before user code starts running
V_{DDP} voltage to ensure defined pad states	V_{DDPPA} CC	–	1.0	–	V	
Start-up time from power-on reset	t_{SSW} SR	–	320	–	µs	Time to the first user code instruction in all start-up modes[4)]
BMI program time	t_{BMI} SR	–	8.25	–	ms	Time taken from a user-triggered system reset after BMI installation is is requested

1) Not all parameters are 100% tested, but are verified by design/characterisation.

2) A capacitor of at least 100 nF has to be added between V_{DDP} and V_{SSP} to fulfill the requirement as stated for this parameter.

3) Valid for a 100 nF buffer capacitor connected to supply pin where current from capacitor is forwarded only to the chip. A larger capacitor value has to be chosen if the power source sink a current.

4) This values does not include the ramp-up time. During startup firmware execution, MCLK is running at 32 MHz and the clocks to peripheral as specified in register CGATSTAT0 are gated.

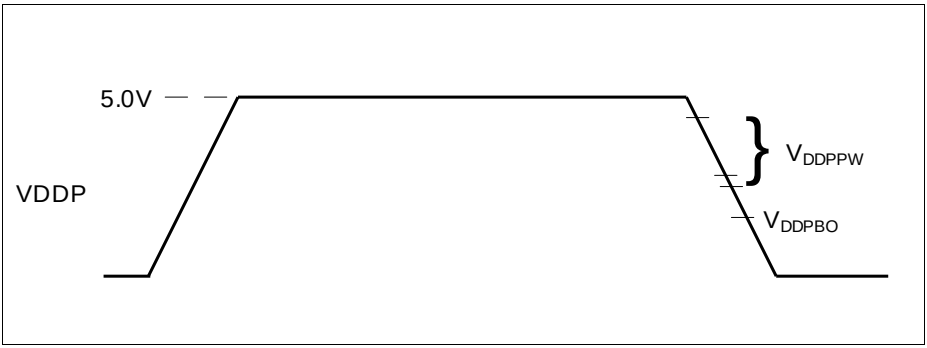

Figure 19 Supply Threshold Parameters

3.3.3 On-Chip Oscillator Characteristics

Note: These parameters are not subject to production test, but verified by design and/or characterization.

Table 25 provides the characteristics of the 64 MHz clock output from the digital controlled oscillator, DCO1 in XMC1200.

Table 25 64 MHz DCO1 Characteristics (Operating Conditions apply)

Parameter	Symbol		Limit Values			Unit	Test Conditions
			Min.	Typ.	Max.		
Nominal frequency	f_{NOM}	CC	–	64	–	MHz	under nominal conditions[1] after trimming
Accuracy[2]	Δf_{LT}	CC	-1.7	–	3.4	%	with respect to f_{NOM}(typ), over temperature (0 °C to 85 °C)
			-3.9	–	4.0	%	with respect to f_{NOM}(typ), over temperature (-40 °C to 105 °C)

1) The deviation is relative to the factory trimmed frequency at nominal V_{DDC} and T_A = + 25 °C.

2) The accuracy of the DCO1 oscillator can be further improved through alternative methods, refer to XMC1000 Oscillator Handling Application Note.

3.3.5 SPD Timing Requirements

The optimum SPD decision time between 0_B and 1_B is 0.75 µs. With this value the system has maximum robustness against frequency deviations of the sampling clock on tool and on device side. However it is not always possible to exactly match this value with the given constraints for the sample clock. For instance for a oversampling rate of 4, the sample clock will be 8 MHz and in this case the closest possible effective decision time is 5.5 clock cycles (0.69 µs).

Table 28 Optimum Number of Sample Clocks for SPD

Sample Freq.	Sampling Factor	Sample Clocks 0_B	Sample Clocks 1_B	Effective Decision Time[1)]	Remark
8 MHz	4	1 to 5	6 to 12	0.69 µs	The other closest option (0.81 µs) for the effective decision time is less robust.

1) Nominal sample frequency period multiplied with 0.5 + (max. number of 0_B sample clocks)

For a balanced distribution of the timing robustness of SPD between tool and device, the timing requirements for the tool are:

- Frequency deviation of the sample clock is +/- 5%
- Effective decision time is between 0.69 µs and 0.75 µs (calculated with nominal sample frequency)

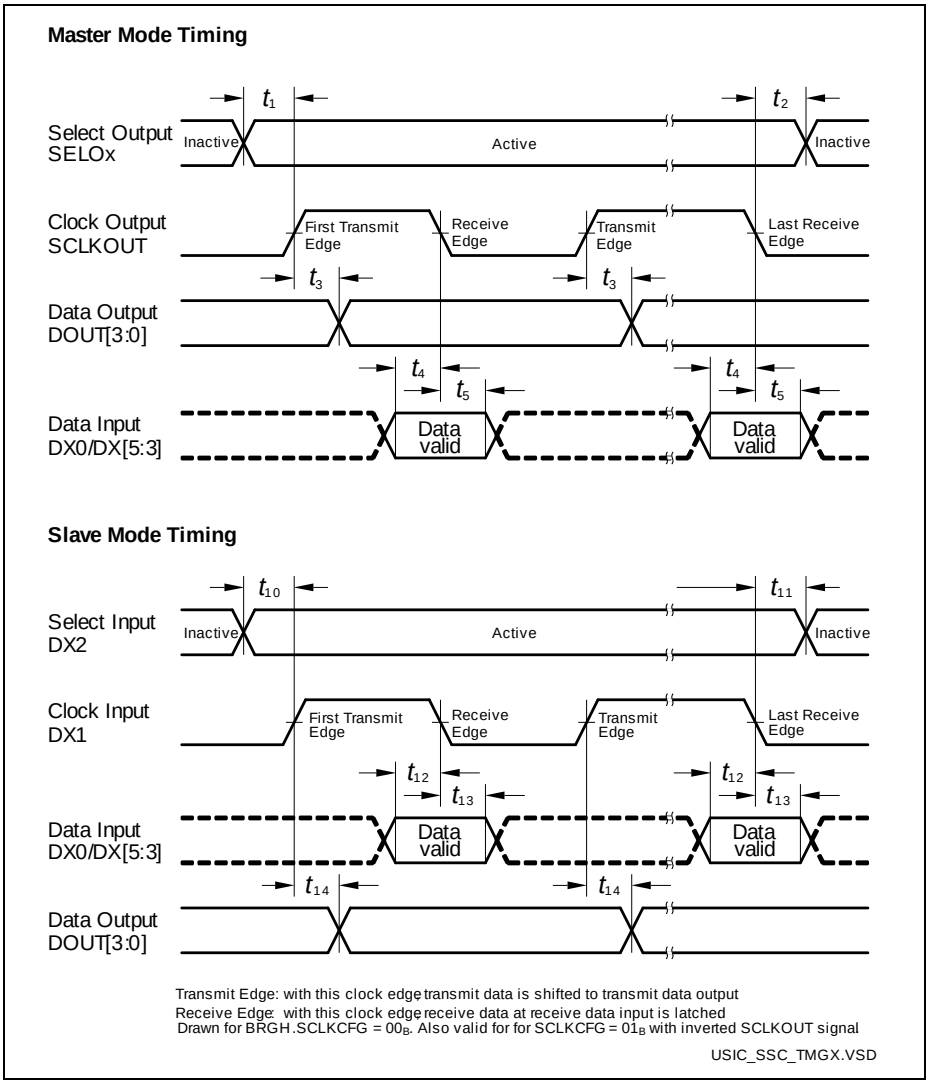

Figure 22 USIC - SSC Master/Slave Mode Timing

Note: This timing diagram shows a standard configuration, for which the slave select signal is low-active, and the serial clock signal is not shifted and not inverted.

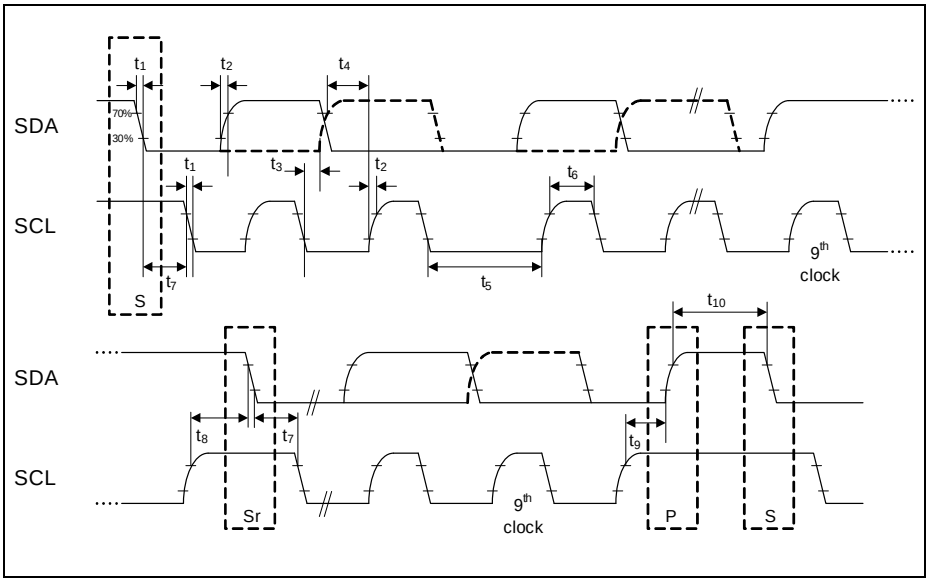

Figure 23 USIC IIC Stand and Fast Mode Timing

3.3.6.3 Inter-IC Sound (IIS) Interface Timing

The following parameters are applicable for a USIC channel operated in IIS mode.

Note: Operating Conditions apply.

Table 33 USIC IIS Master Transmitter Timing

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Clock period	t_1 CC	$2/f_{MCLK}$	-	-	ns	$V_{DDP} \geq 3$ V
		$4/f_{MCLK}$	-	-	ns	$V_{DDP} < 3$ V
Clock HIGH	t_2 CC	0.35 x t_{1min}	-	-	ns	
Clock Low	t_3 CC	0.35 x t_{1min}	-	-	ns	
Hold time	t_4 CC	0	-	-	ns	
Clock rise time	t_5 CC	-	-	0.15 x t_{1min}	ns	

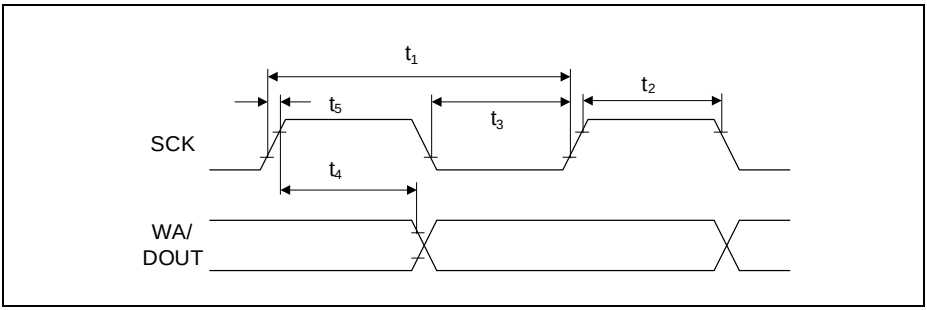

Figure 24 USIC IIS Master Transmitter Timing

Table 34 USIC IIS Slave Receiver Timing

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Clock period	t_6 SR	$4/f_{MCLK}$	-	-	ns	
Clock HIGH	t_7 SR	0.35 x t_{6min}	-	-	ns	
Clock Low	t_8 SR	0.35 x t_{6min}	-	-	ns	
Set-up time	t_9 SR	0.2 x t_{6min}	-	-	ns	
Hold time	t_{10} SR	10	-	-	ns	

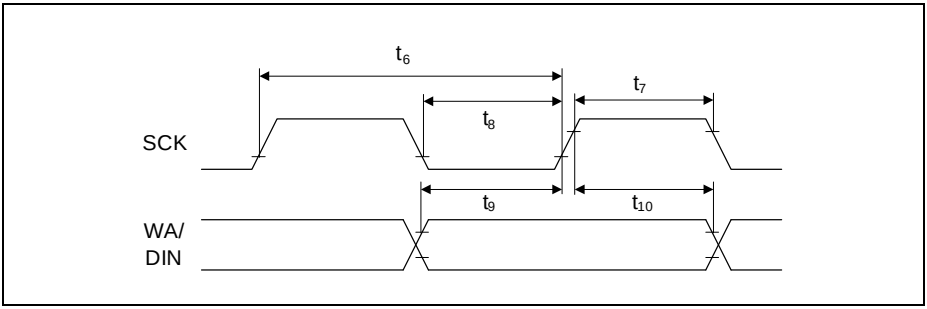

Figure 25 USIC IIS Slave Receiver Timing

4 Package and Reliability

The XMC1200 is a member of the XMC™1000 Family of microcontrollers. It is also compatible to a certain extent with members of similar families or subfamilies.

Each package is optimized for the device it houses. Therefore, there may be slight differences between packages of the same pin-count but for different device types. In particular, the size of the exposed die pad may vary.

If different device types are considered or planned for an application, it must be ensured that the board layout fits all packages under consideration.

4.1 Package Parameters

Table 35 provides the thermal characteristics of the packages used in XMC1200.

Table 35 Thermal Characteristics of the Packages

Parameter	Symbol	Limit Values		Unit	Package Types
		Min.	Max.		
Exposed Die Pad Dimensions	Ex × Ey CC	-	2.7 × 2.7	mm	PG-VQFN-24-19
		-	3.7 × 3.7	mm	PG-VQFN-40-13
Thermal resistance Junction-Ambient	$R_{\Theta JA}$ CC	-	104.6	K/W	PG-TSSOP-16-8[1)]
		-	83.2	K/W	PG-TSSOP-28-16[1)]
		-	70.3	K/W	PG-TSSOP-38-9[1)]
		-	46.0	K/W	PG-VQFN-24-19[1)]
		-	38.4	K/W	PG-VQFN-40-13[1)]

1) Device mounted on a 4-layer JEDEC board (JESD 51-5); exposed pad soldered.

Note: For electrical reasons, it is required to connect the exposed pad to the board ground V_{SSP}, independent of EMC and thermal requirements.

4.1.1 Thermal Considerations

When operating the XMC1200 in a system, the total heat generated in the chip must be dissipated to the ambient environment to prevent overheating and the resulting thermal damage.

The maximum heat that can be dissipated depends on the package and its integration into the target board. The “Thermal resistance $R_{\Theta JA}$” quantifies these parameters. The power dissipation must be limited so that the average junction temperature does not exceed 115 °C.

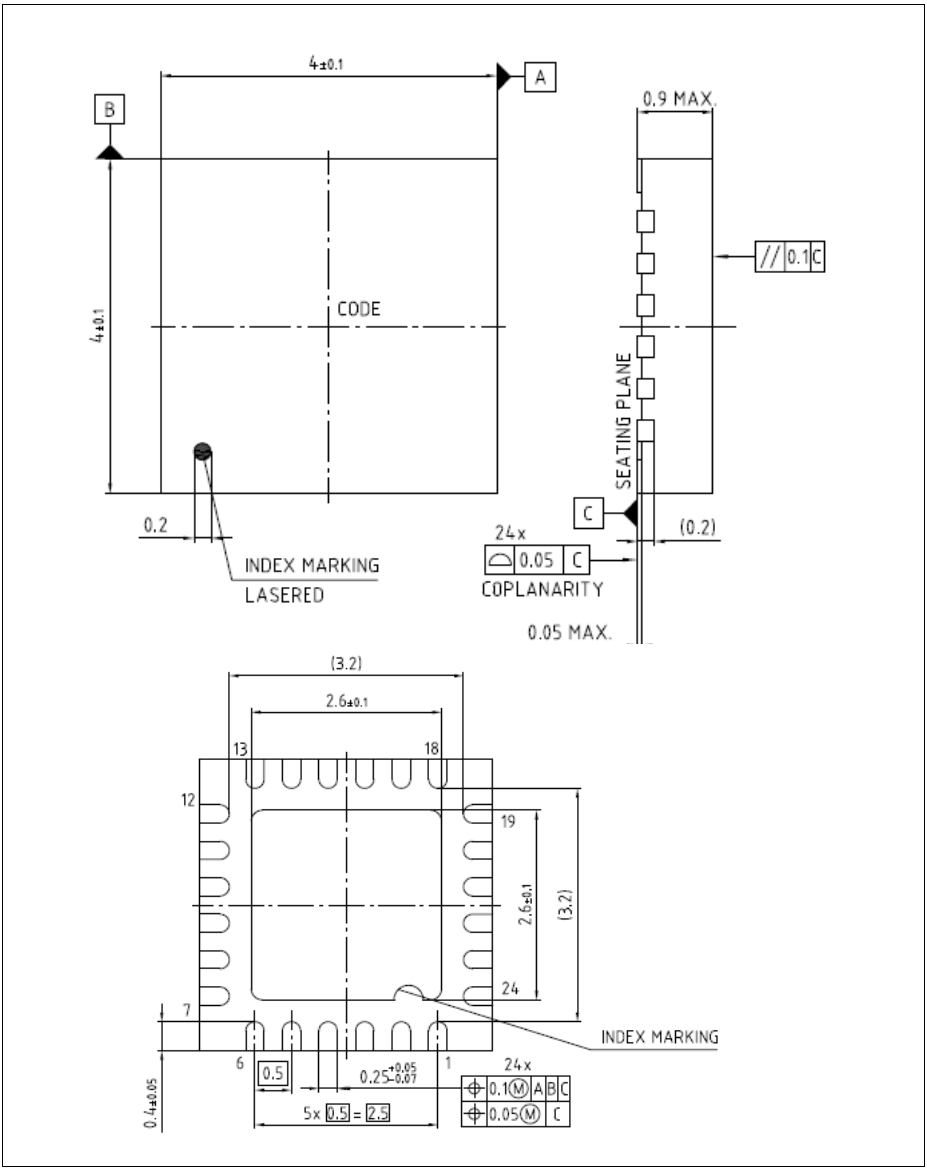

Figure 29 PG-VQFN-24-19

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